Localization in an Inhomogeneous Interacting Quantum Wire

Jiang Qian Physics Department, Harvard University Physics Department, Peking University, October 9th, 2008

Collaborations and Acknowledgments

- Theory: Gregory A. Fiete, Yaroslav Tserkovnyak, Bertrand Halperin
- Experiments: Hadar Steinberg, Ophir Auslaender, Amir Yacoby
- Acknowledgment: Walter Hofstetter, Gergely Zarand

Papers:

- cond-mat/0501684 (PRB 72, 045315)
- cond-mat/0506812 (PRB 73, 113307)
- arXiv:0707.2992 (PRB 77, 085314)

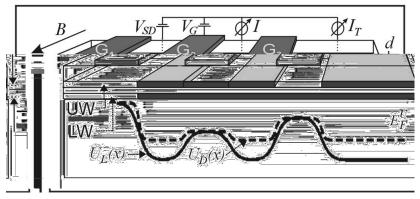
Luttinger Liquid and Momentum Resolved Tunneling between Quantum Wires

Luttinger liquid model of 1D interacting quantum system

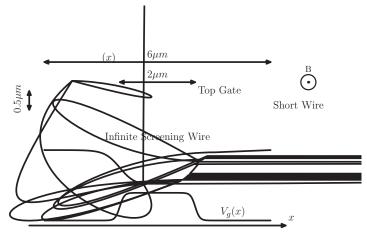
- The Luttinger liquid is a **stable xed point** of 1D quantum systems with gapless excitations
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Schematic Diagram of Experimental Setup



Tunneling conductance is $G = dI_T/dV_{SD}$. Experiments measure dG/dV_g to pick out physics sensitive to density.



Model geometry, charge density distribution r(x) and gate voltage V_q

Theory of Tunneling Conductance

At zero temperature, only the tunneling between ground states contributes. The tunneling conductance $G \mu |M(k_+)|^2 + |M(k_-)|^2$, where

$$k_{\pm} = \pm k_F^{lower} + e \mathbf{B} d / \hbar$$
,

and

$$M(k) = \langle Y^N | c_k^{\dagger} | Y^{N-1} \rangle$$
.

It is instructive to de ne a \quasi-wavefunction":

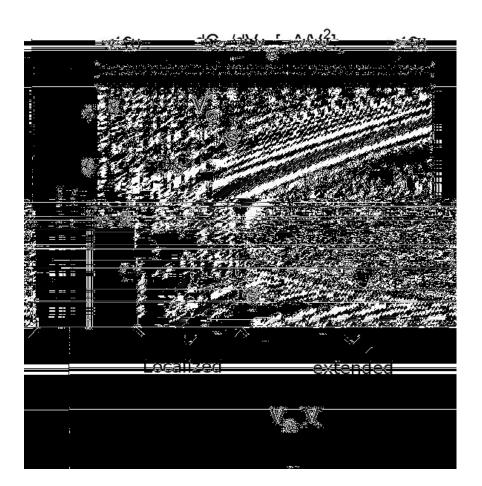
$$Y_{\text{eff}}^{\textit{N}}(\textit{x}) \equiv \langle Y_{\textit{g}}^{\textit{N}-1} | y_{\textit{s}}(\textit{x}) | Y_{\textit{a}}^{\textit{N}} \rangle \; , \label{eq:Yeff}$$

then

$$M(k) = \frac{Z}{dx e^{ikx} Y_{\text{eff}}^{N*}(x)}.$$

For non-interacting wire Y_{eff}^{N} is simply the wavefunction of last occupied electron.

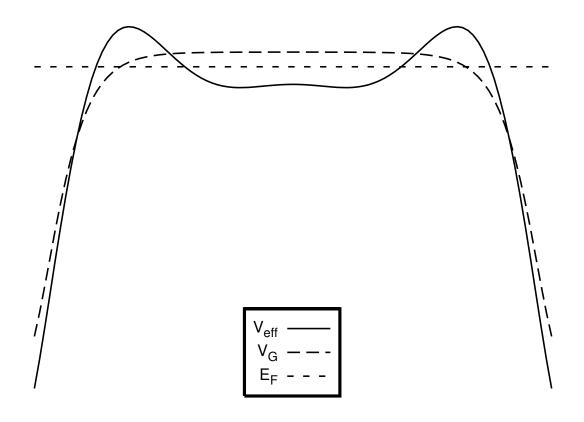
Overall Features of Experimental Data



Key Features:

- Extended state: density n changes continuously with gate voltage V_g , momentum dependence of tunneling sharply peaked at $k = \pm k_F(n)$.
- Localized state: density n changes discretely with gate voltage V_g , momentum dependence of tunneling extended over a wide range of k.

Self-consistent Con ning Potential Generated by Interaction?



hypothetical self-consistent potential in the localized phase

Part I: Momentum Dependence of Tunneling Conductance

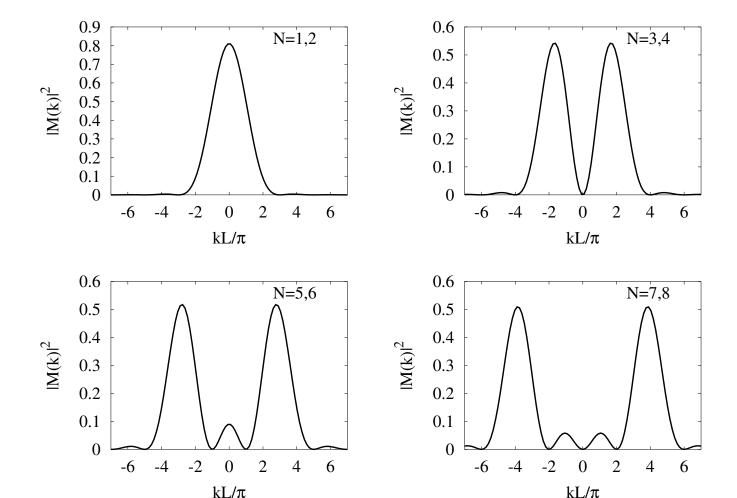


Basic features of momentum distribution:

- Broad momentum distribution, implying localized electrons
- Typically two broad peaks, the separation between which widens with increasing particle number *N*
- Last Coulomb blockade peak has single peak in momentum distribution

Non-interacting Electrons, T = 0, Box with Hard Wall

As large N, $|M(k)|^2$ becomes peaked at $k_N = Np/L$ with width dk = 2p/L.

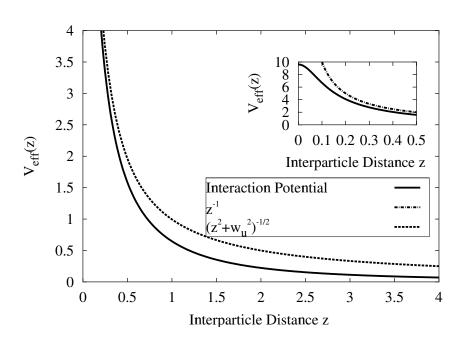


Screened Coulomb Interaction Potential

The Coulomb interaction in the short upper wire is assumed to have a **short-range** cuto due to the nite width of the wire and long-range cuto due to screening by the more conducting lower wire.

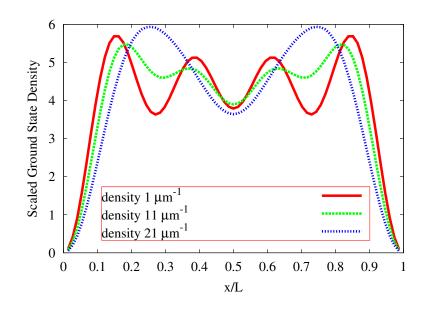
$$ilde{V}_{\mathrm{eff}}(q) = ilde{V}_{0}(q, W_{u}) - rac{ ilde{V}_{0}^{2}(q, d)}{ ilde{V}_{0}(q, W_{l})}$$

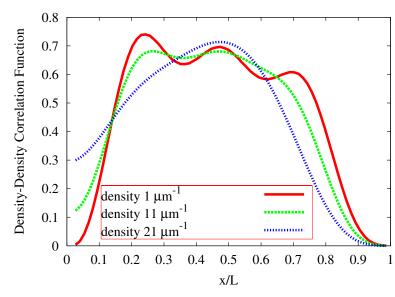
 $\tilde{V}_{eff}(q) = \tilde{V}_0(q, \mathcal{W}_u) - \frac{\tilde{V}_0^2(q, d)}{\tilde{V}_0(q, \mathcal{W}_l)} \,,$ where $\tilde{V}_0(q, \mathcal{W}) = {R_{\neq} \atop -\neq}} dx \frac{e^{iqx}}{\sqrt{x^2 + \mathcal{W}^2}} = 2 \mathcal{K}_0(\mathcal{W}q). \,\, \mathcal{K}_0$ is modi ed Bessel function.



Formation of Quasi-Wigner Crystal Order with Lowering Density

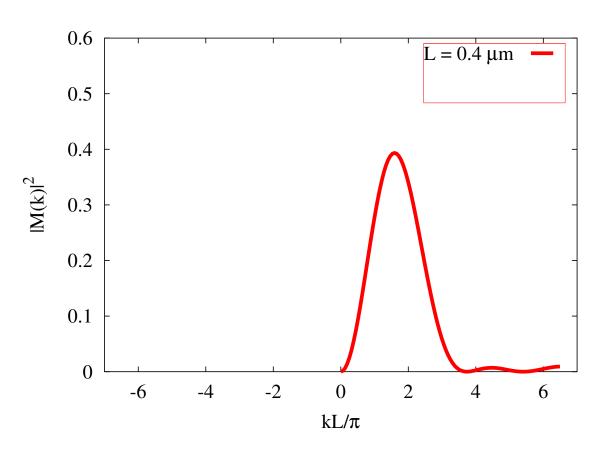
Instead of the Friedel oscillation of frequency $2k_F$, clear oscillations of frequency $4k_F$ show up, both in density and in density-density-correlation, at low density. Here density-density correlation function is de ned as $\frac{1}{1-x} {n\choose 0} r(x') r(x'+x) dx'$.





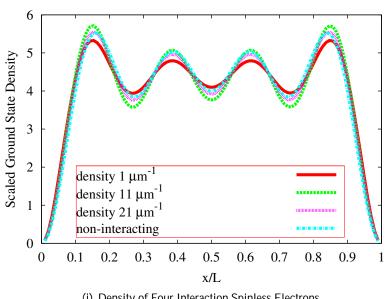
Ground State Tunneling: Exact-Diagonalization

 $|M(k)|^2$ is insensitive to interactions. Following plot show $|M(k)|^2$ for tunneling from N=3 to N=4 state.

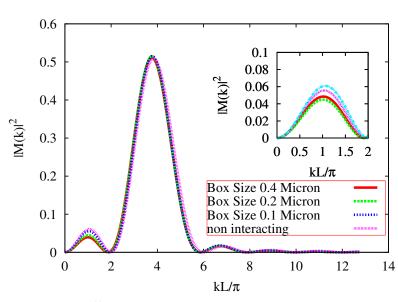


Spinless/Polarized Electrons

Under the experimental parameters, spinless electrons are essentially non-interacting for both high and low density.



(i) Density of Four Interaction Spinless Electrons



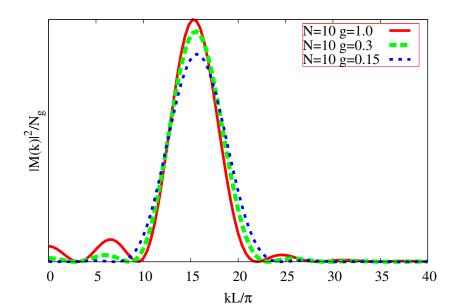
(j) Tunneling of Three to Four spinless Electron

Large-N limit: Ground State Tunneling

For large but nite N and not too close to wall, Luttinger liquid theory gives an estimate of the ground state quasi-wavefunction as de ned before:

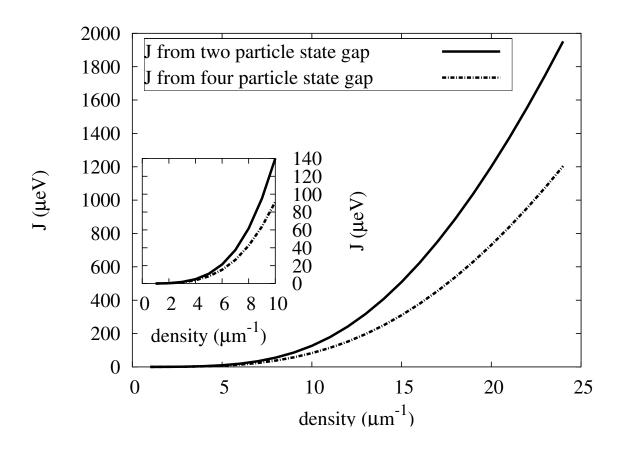
$$Y_{\text{eff}}^{N}(x) \sim \frac{1}{\sqrt{LN^a}} \sin \frac{px}{L} i \frac{1}{2} (a_{\text{end}} - a) \sin(k_F x),$$

where tunneling exponent for bulk and end is given by Luttinger liquid interaction parameter g as $a = (g+g^{-1}-2)/4$ and $a_{end} = (g^{-1}-1)/2$, respectively. A normalization factor N_g is used so that the integrated areas under the three curves are the same.



Estimates of E ective Heisenberg Exchange Constant J

At strong interaction, the dynamics of system can be described by Heisenberg model. The Heisenberg exchange parameter J can be extracted from gap D between ground state and rst excited state. For N = 2 J = D and for N = 4 J = 1.5178D.



Tunneling Conductance at Finite Temperature

Total Conductance
$$G = C(\mathcal{B}(k_+) + \mathcal{B}(k_-))$$
, where
$$\mathcal{B}(k) = \underset{ags}{\mathring{a}} |\langle Y_a^N | c_{ks}^\dagger | Y_g^{N-1} \rangle|^2 W_{ag},$$

$$W_{ag} = e^{-b[E_g^{N-1} - m(N-1)]} f(e_{ag})$$

$$= e^{-b(E_a^N - mN)} [1 - f(e_{ag})],$$

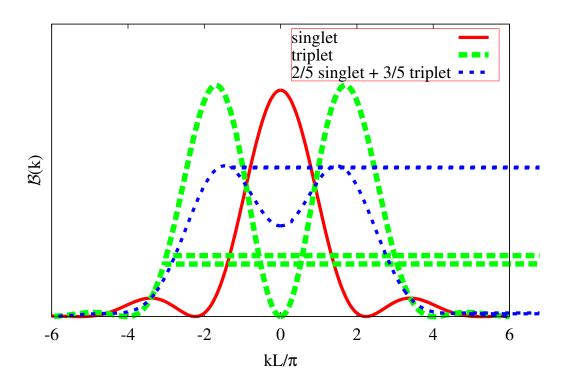
$$k_{\pm} = \pm k_F^J + eBd/h.$$

$$e_{ag} = E_a^N - E_g^{N-1},$$

$$C = \frac{pe^2}{2h} I^2 bnL \frac{e^{-bmN}}{Z_N + e^{-bm}Z_{N-1}},$$

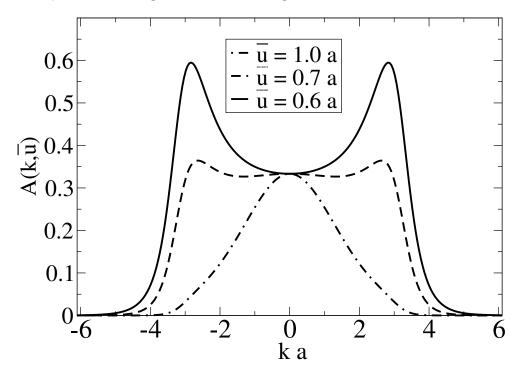
Finite Temperature and Mixing Spins: Exact Diagonalization

For strong repulsive interaction, spin excitation energy scale D = J/N may become very small. Three energies scales are important: spin gap D, Zeeman energy E_Z and thermal energy k_BT . Following picture shows tunneling from N = 1 to N = 2: the case of singlet ground state $(E_Z < D)$, triplet ground state $(E_Z > D)$ and high temperature mixed state $(E_Z, D \ll k_BT \ll D_{charge})$.



Finite Temperature and Mixing Spins: Free Spin Regime and Large N limit

If $J \ll k_B T \ll \hbar v_c k_F$, spin con gurations have equal thermal weight but there's no charge excitation, we not a spectral weight as following:



Here $\bar{u} = \frac{a}{p}^{\bigcap} \overline{2g \ln(L/a)}$ is the root-mean-square uctuation of electron position. g is the Luttinger liquid interaction parameter.

Conclusions for Part I

We investigated the momentum dependence of tunneling matrix elements from a in nite wire into short quantum containing interacting electrons.

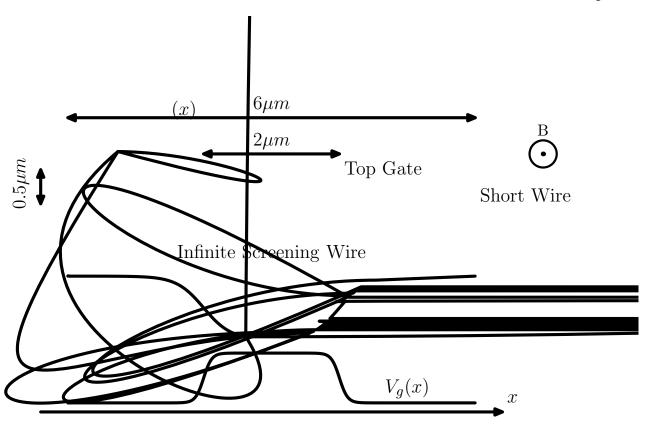
- For $N \le 4$ exact diagonalization is carried out, ground state tunneling matrix element $|M(k)|^2$ is computed.
- Large N calculations of tunneling amplitude, both for ground state tunneling and for free spin regime, are carried out using Luttinger liquid theory.

Other Possible Factors in Accounting for Experimental Observation

- Soft instead of hard wall con nement: more spectral weight at center.
- Partial spin polarization
- Asymmetry of con nement potential

Part II: Electronic States of Low Density Region

Model geometry for the electronic density distribution r(x) and gate potential $V_g(x)$



The Restricted Hartree-Fock Hamiltonian

Assumptions and simpli cations of the Hartree-Fock model:

- Spin restricted to be either aligned or anti-aligned with magnetic eld B
- Two subbands corresponding to di erent transverse modes in the quantum wire
- Electrons in di erent subbands interact only through Hartree terms

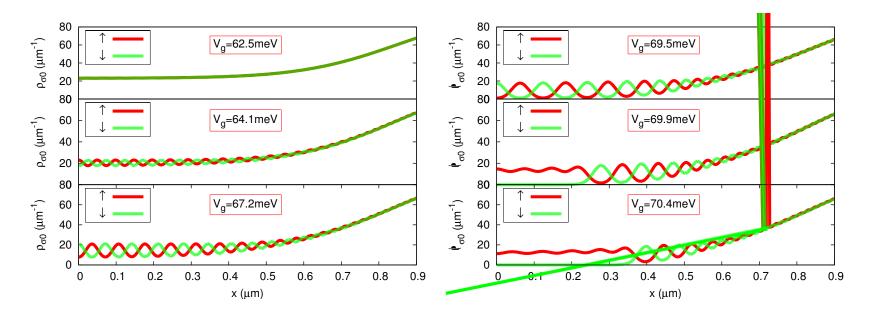
$$Hy_{sb}(x) = -\frac{\hbar^{2}}{2m^{*}} \frac{\P^{2}y_{sb}(x)}{\P x^{2}} + (V_{G}(x) + D_{b})y_{sb}(x) + m_{B}BS_{z}y_{sb}(x) + V_{H}(x)y_{sb}(x) - dx'V_{F}^{sb}(x,x')y_{sb}(x')$$

$$V_{H}(x) = \frac{Z}{dx'(\mathop{\mathring{a}}_{i,s',b'}|y_{is'b}(x')|^{2})V_{eff}(x-x')}$$

$$V_{F}^{sb} = \mathop{\mathring{a}}_{i}y_{isb}(x)y_{isb}^{*}(x')V_{eff}(x-x').$$

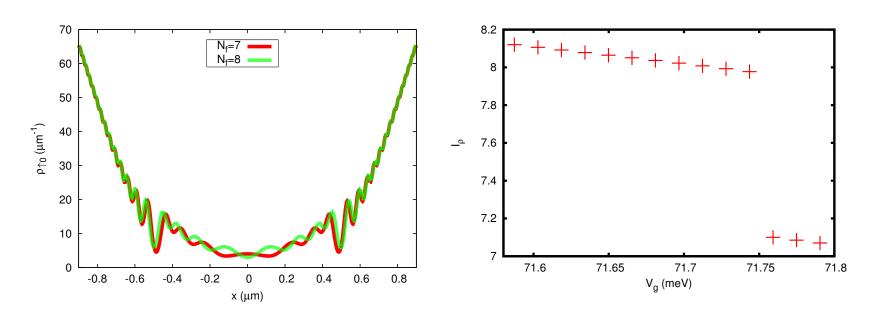
Magnetic Phases at the Low Density Region

- The emergence of an antiferromagnetic order at the low density region (left)
- The emergence of spin-aligned region at the center of the wire (right)



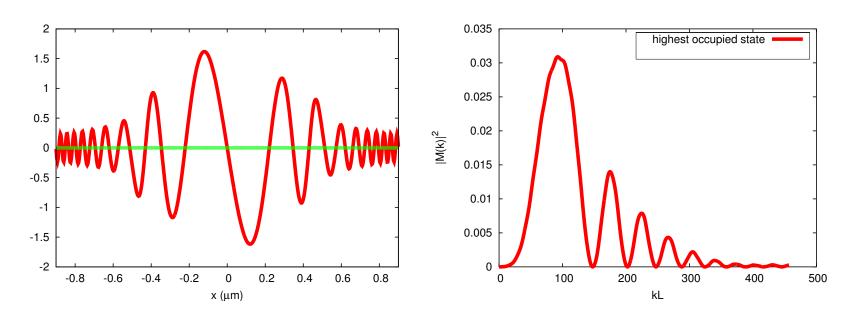
Discrete Density Changes in the Spin-aligned Phase

Abrupt density rearrangements occur due to the successive expulsion of a single electron from the spin-aligned region



Nature of Electronic States in the Spin-aligned Region

- The wavefunctions near the Fermi level have large weights near the center
- No sign of self-consistent barrier at the ends of spin-aligned region
- Little spectral weight near k = 0 in the momentum-dependent tunneling matrix element



Left wavefunction of N = 7 solution at E_f Right transition from N = 7 to N = 8 solutions

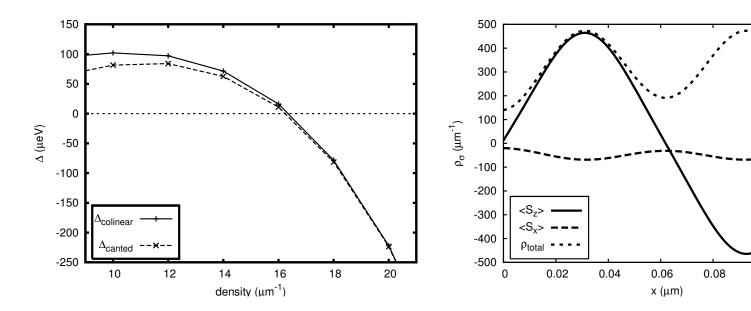
Unrestricted Hartree-Fock in a Homogeneous system: E ects of Canting in the Antiferromagnetic Phase

- The correction to the energy per unit cell due to canting is small in the range where the ground state is antiferromagnetic
- The S_x magnetization is small for canted solution at $r = 16mm^{-1}$, where the system make a transition to a ferromagnetic ground state

ρ_{total} (μm⁻¹

0.12

0.1



Conclusions for Part II

We investigated the density and spin con guration an inhomogeneous quantum wire using the restricted Hartree-Fock method. We found:

- When lowering its density, the depleted region goes from a non-magnetic state to an antiferromagnetic state, and nally to a spin-aligned state sandwiched by antiferromagnetic states
- In the spin-aligned phase, the spin-aligned region undergoes abrupt density changes by successively losing a single electron
- The wavefunctions near the Fermi surface are relatively localized near the center, but they are not Coulomb-blockade states con ned by barrier potentials
- Additional mechanisms, such as impurity potentials or multiple spin state contributions, are needed to explain the observed large spectral weigh near k = 0 in the momentum dependent tunneling
- In our model, the e ects due to the canting of the spins in the unrestricted Hartree-Fock model are small